

CoolMOS™ Power Transistor
Features

- Low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant

Product Summary

| | | |
|------------------|------|----------|
| V_{DS} | 650 | V |
| $R_{DS(on),max}$ | 0.28 | Ω |
| $Q_{g,typ}$ | 63 | nC |

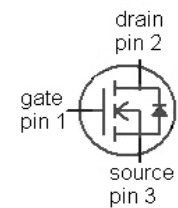
CoolMOS C3 designed for:

- Notebook Adapter

TO-262-3-1



| Type | Package | Marking |
|------------|-------------|---------|
| SPI15N65C3 | P-TO262-3-1 | 15N65C3 |


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|---|----------------|--------------------------------------|-------------|--------------------|
| Continuous drain current | I_D | $T_C=25\text{ °C}$ | 15 | A |
| | | $T_C=100\text{ °C}$ | 9.4 | |
| Pulsed drain current ³⁾ | $I_{D,pulse}$ | $T_C=25\text{ °C}$ | 45 | |
| Avalanche energy, single pulse | E_{AS} | $I_D=3\text{ A}, V_{DD}=50\text{ V}$ | 460 | mJ |
| Avalanche energy, repetitive t_{AR} ^{2),3)} | E_{AR} | $I_D=5\text{ A}, V_{DD}=50\text{ V}$ | 0.8 | |
| Avalanche current, repetitive t_{AR} ^{3),4)} | I_{AR} | | 5.0 | A |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS}=0\dots480\text{ V}$ | 50 | V/ns |
| Gate source voltage | V_{GS} | static | ± 20 | V |
| | | AC ($f>1\text{ Hz}$) | ± 30 | |
| Power dissipation | P_{tot} | $T_C=25\text{ °C}$ | 156 | W |
| Operating and storage temperature | T_j, T_{stg} | | -55 ... 150 | $^{\circ}\text{C}$ |

Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|--|---------------|--------------------------------|-------|------|
| Continuous diode forward current ²⁾ | I_S | $T_C=25\text{ }^\circ\text{C}$ | 15 | A |
| Diode pulse current ³⁾ | $I_{S,pulse}$ | | 45 | |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|--|------------|---------------------------------------|---|---|-----|------------------|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 0.8 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | leaded | - | - | 62 | |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | 1.6 mm (0.063 in.) from case for 10 s | - | - | 260 | $^\circ\text{C}$ |

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified
Static characteristics

| | | | | | | |
|----------------------------------|---------------|--|-----|------|------|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$ | 650 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_D=0.675\text{ mA}$ | 2.1 | 3 | 3.9 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ }^\circ\text{C}$ | - | 0.5 | 25 | μA |
| | | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ }^\circ\text{C}$ | - | 25 | - | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}$, $I_D=9.4\text{ A}$, $T_j=25\text{ }^\circ\text{C}$ | - | 0.25 | 0.28 | Ω |
| | | $V_{GS}=10\text{ V}$, $I_D=9.4\text{ A}$, $T_j=150\text{ }^\circ\text{C}$ | - | 0.68 | - | |
| Gate resistance | R_G | $f=1\text{ MHz}$, open drain | - | 1.4 | - | Ω |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|--|--------------|---|---|------|---|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$ | - | 1600 | - | pF |
| Output capacitance | C_{oss} | | - | 540 | - | |
| Effective output capacitance, energy related ⁵⁾ | $C_{o(er)}$ | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V | - | 67 | - | |
| Effective output capacitance, time related ⁶⁾ | $C_{o(tr)}$ | | - | 120 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=15\text{ A},$ $R_G=6.8\ \Omega$ | - | 32 | - | ns |
| Rise time | t_r | | - | 14 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 70 | - | |
| Fall time | t_f | | - | 11 | - | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|---------------|---|---|-----|---|----|
| Gate to source charge | Q_{gs} | $V_{DD}=480\text{ V}, I_D=15\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 9 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 29 | - | |
| Gate charge total | Q_g | | - | 63 | - | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.4 | - | V |

Reverse Diode

| | | | | | | |
|-------------------------------|-----------|---|---|-----|-----|---------------|
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=15\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 1.0 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=480\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 420 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 8 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 32 | - | A |

¹⁾ J-STD20 and JESD22

²⁾ Limited only by maximum temperature.

³⁾ Pulse width t_p limited by $T_{j,max}$

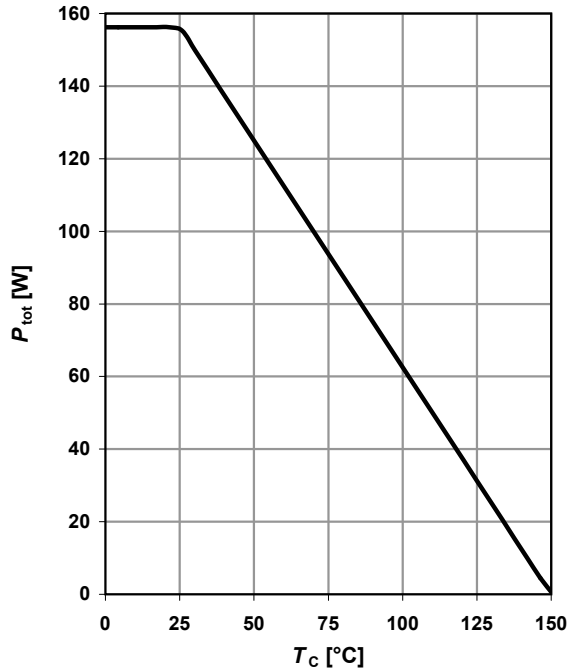
⁴⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

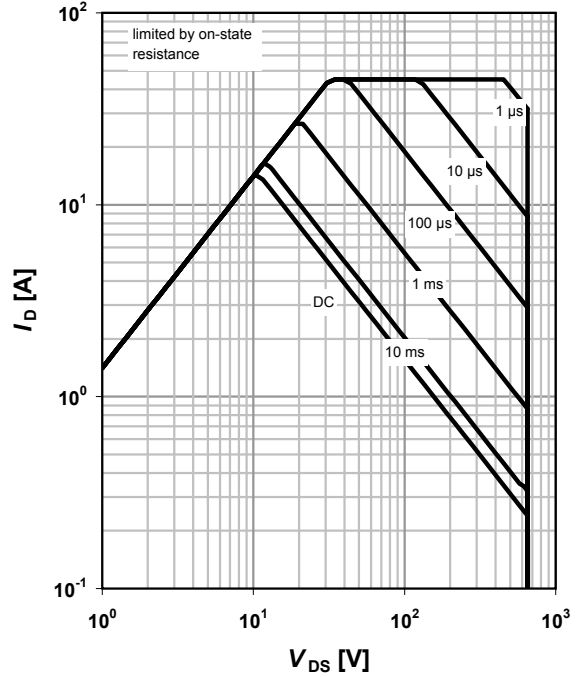
$$P_{tot} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

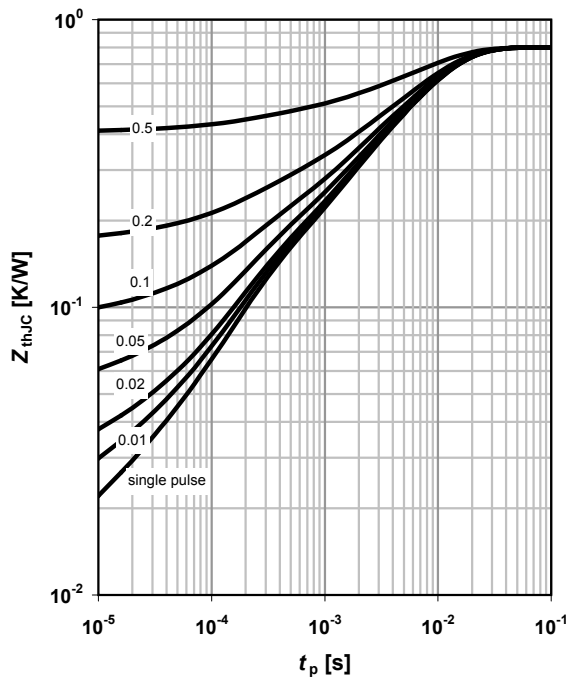
parameter: t_p



3 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

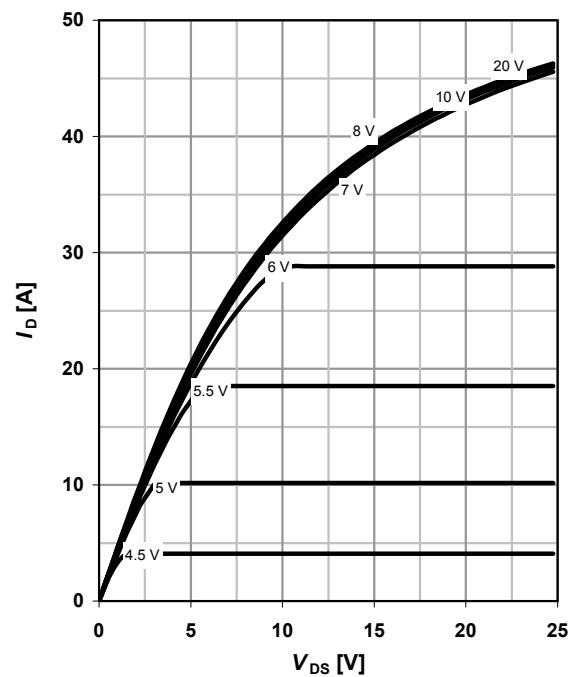
parameter: $D = t_p / T$



4 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

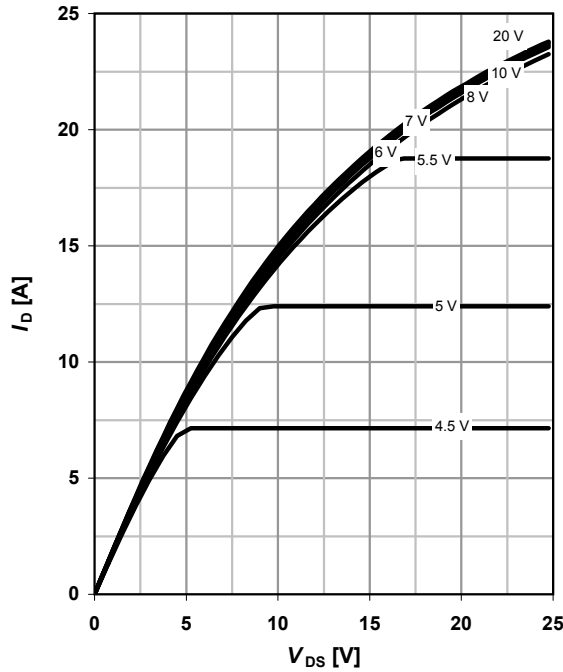
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ }^\circ\text{C}$

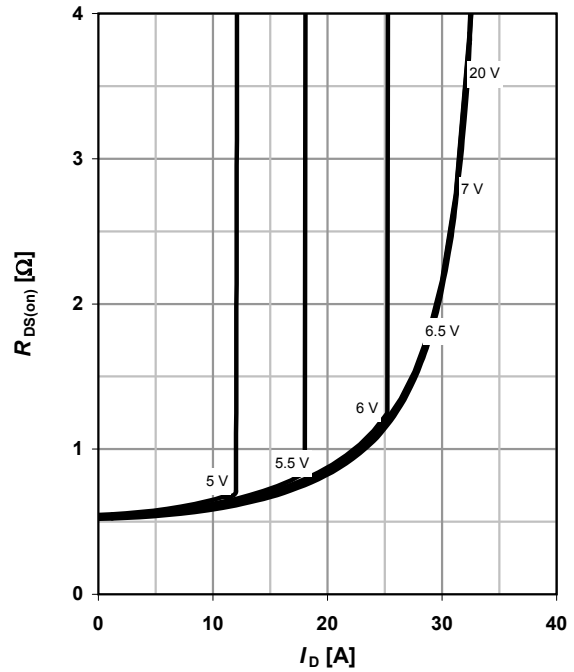
parameter: V_{GS}



6 Typ. drain-source on-state resistance

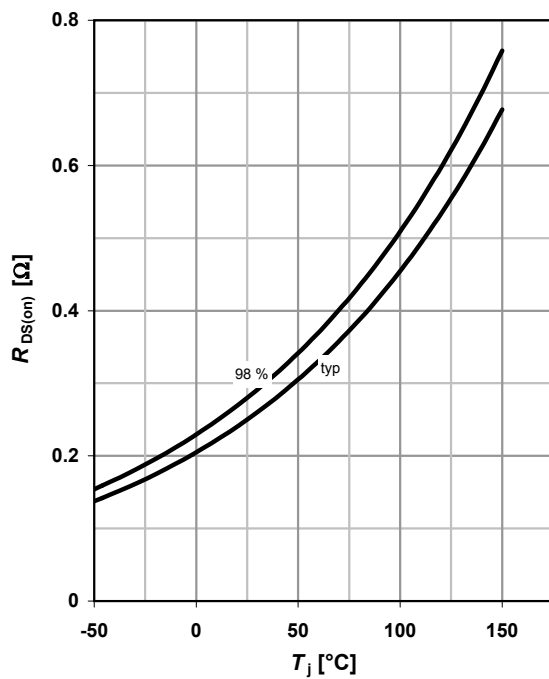
$R_{DS(on)} = f(I_D); T_j = 150\text{ }^\circ\text{C}$

parameter: V_{GS}



7 Drain-source on-state resistance

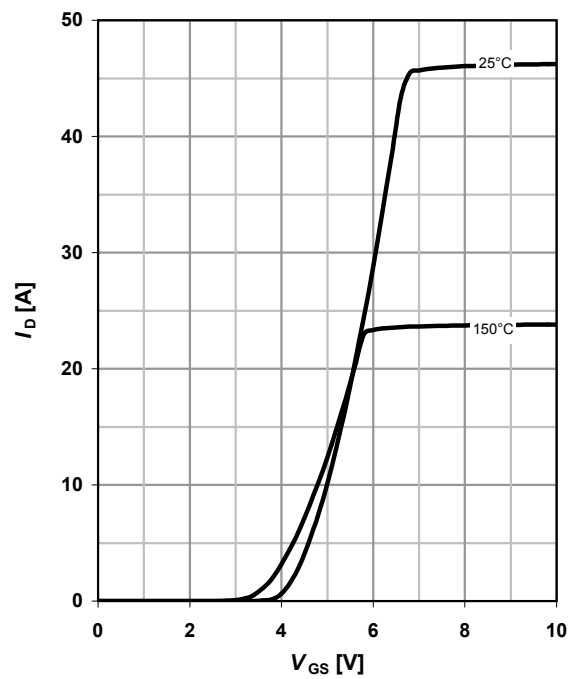
$R_{DS(on)} = f(T_j); I_D = 9.4\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

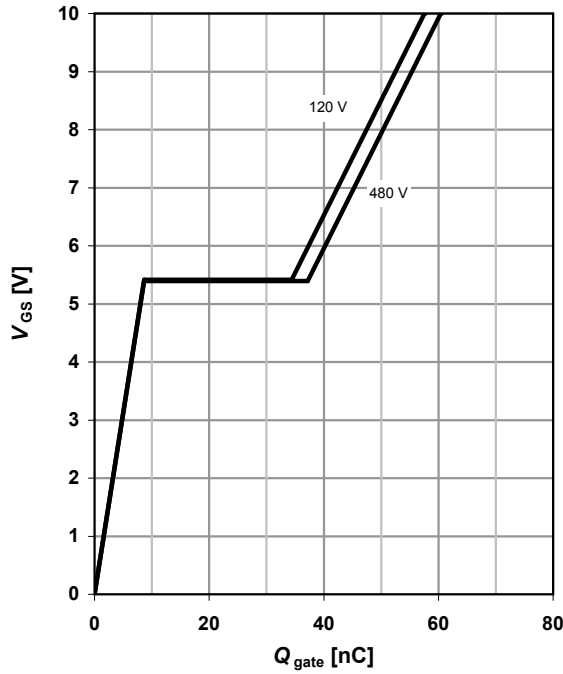
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=15\text{ A pulsed}$

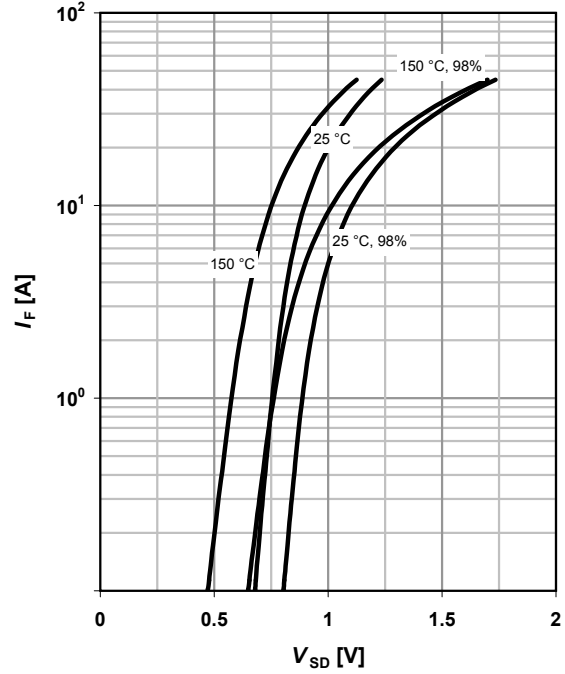
parameter: V_{DD}



10 Forward characteristics of reverse diode

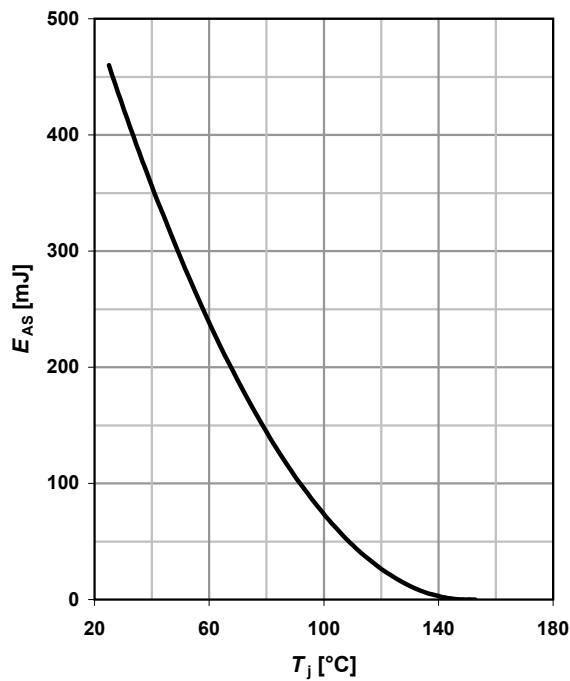
$I_F=f(V_{SD})$

parameter: T_j



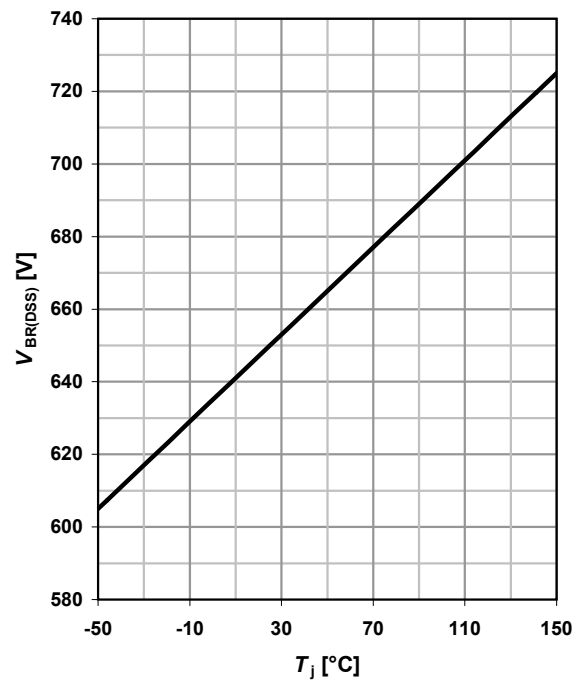
11 Avalanche energy

$E_{AS}=f(T_j); I_D=3\text{ A}; V_{DD}=50\text{ V}$



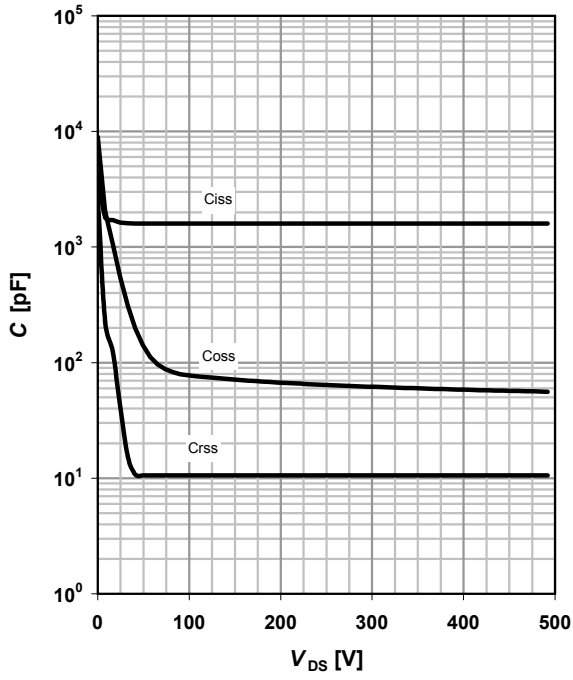
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



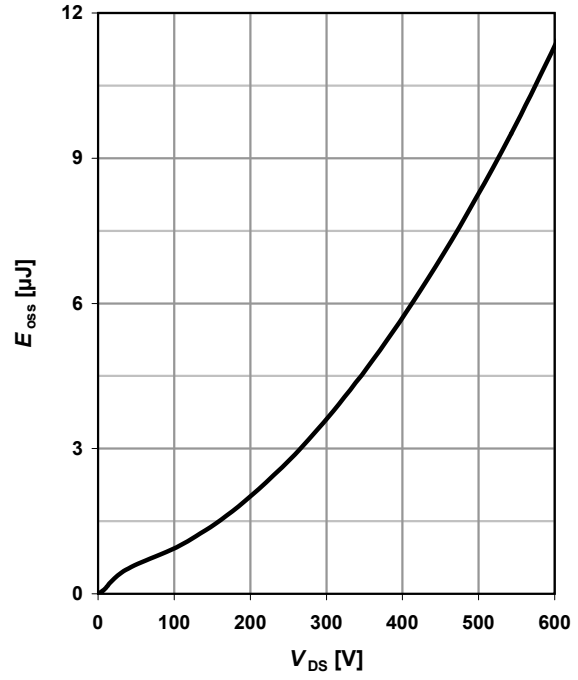
13 Typ. capacitances

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



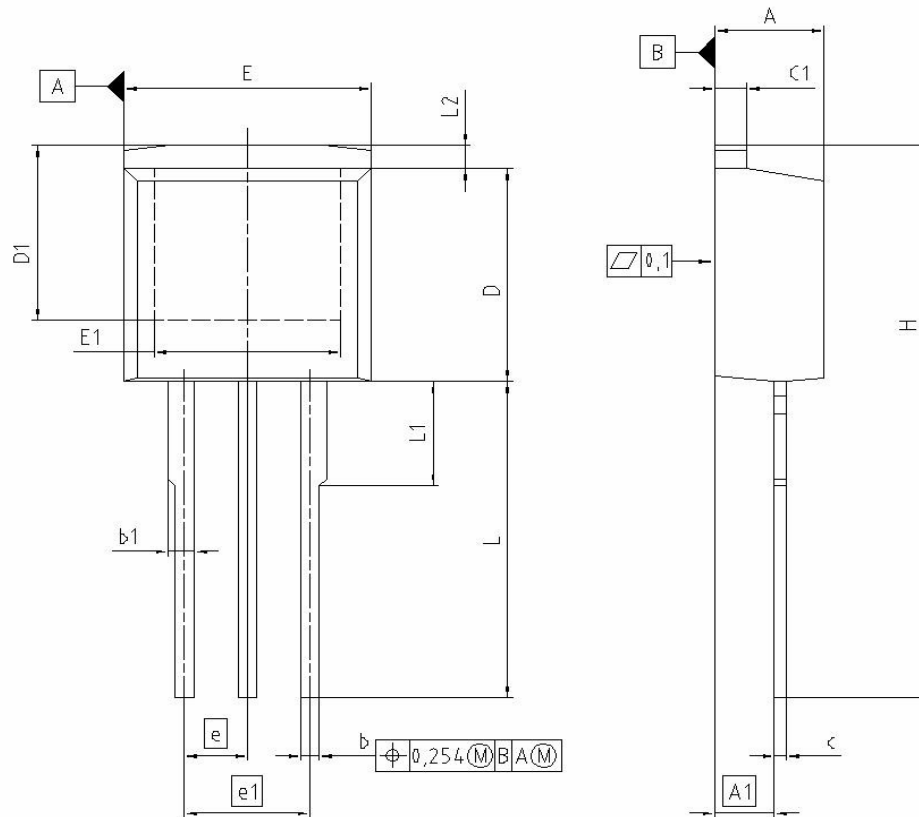
14 Typ. Coss stored energy

$E_{oss}=f(V_{DS})$



Definition of diode switching characteristics





| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|--------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.300 | 4.500 | 0.169 | 0.177 |
| A1 | 2.150 | 2.650 | 0.085 | 0.104 |
| b | 0.650 | 0.850 | 0.026 | 0.033 |
| b1 | 0.635 | 1.400 | 0.025 | 0.055 |
| c | 0.400 | 0.600 | 0.016 | 0.024 |
| c1 | 1.170 | 1.370 | 0.046 | 0.054 |
| D | 9.050 | 9.450 | 0.356 | 0.372 |
| D1 | 6.900 | 7.650 | 0.272 | 0.301 |
| E | 9.800 | 10.200 | 0.386 | 0.402 |
| E1 | 7.250 | 8.600 | 0.285 | 0.339 |
| e | 2.540 | | 0.100 | |
| e1 | 5.080 | | 0.200 | |
| N | 3 | | 3 | |
| L | 13.000 | 14.000 | 0.512 | 0.551 |
| L1 | 4.350 | 4.750 | 0.171 | 0.187 |
| L2 | 0.700 | 1.300 | 0.028 | 0.051 |

REFERENCE
JEDEC TO262

SCALE

EUROPEAN PROJECTION

ISSUE DATE
01-06-2005

FILE
TO262_1

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